

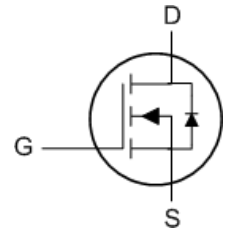
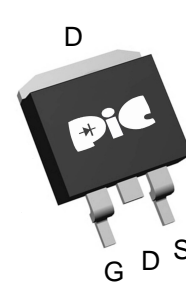
➤ General Description

This PAN90TP04SP N-Channel enhancement mode power field effect transistor is the high density technology and this advanced technology can provide excellent $R_{ds(On)}$ performance and efficiency for power switching and load switching application., this device also comply with the RoHS and Green Product requirement with full function reliability approved.

➤ Feature

- Super Low Gate Charge
- Green Device Available Excellent
- Cdv/dt effect decline
- Advanced high cell densit Trench
- TO-263-2L package design

➤ TO-263-2L



➤ Application

- DC-DC Converters
- Power Management
- Analog Switch

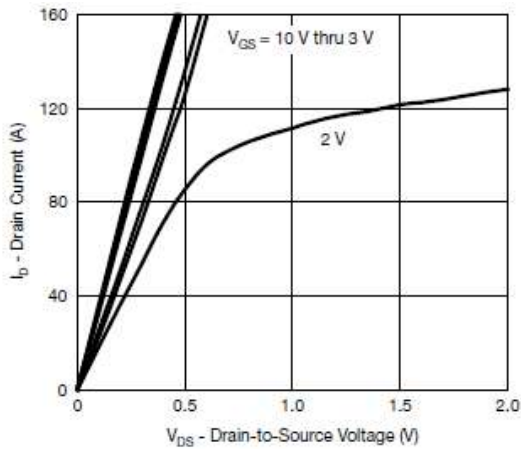
➤ Absolute Maximum Ratings

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DSS}	40	V
Gate -Source Voltage	V_{GSS}	± 20	V
Continuous Drain Current($T_J=150^\circ C$)	I_D	$T_C=25^\circ C$	90
		$T_C=70^\circ C$	90
Pulsed Drain Current	I_{DM}	160	A
Continuous Source Current(Diode Conduction)	I_S	80	
Single Pulse Avalanche Current	I_{AS}	40	
Power Dissipation	P_D	$T_C=25^\circ C$	250
		$T_A=25^\circ C$	3.75
Operating Junction Temperature	T_J	150	$^\circ C$
Storage Temperature Range	T_{STG}	-55/150	$^\circ C$
Thermal Resistance-Junction to Ambient	$R_{\theta JA}$	62.5	$^\circ C/W$

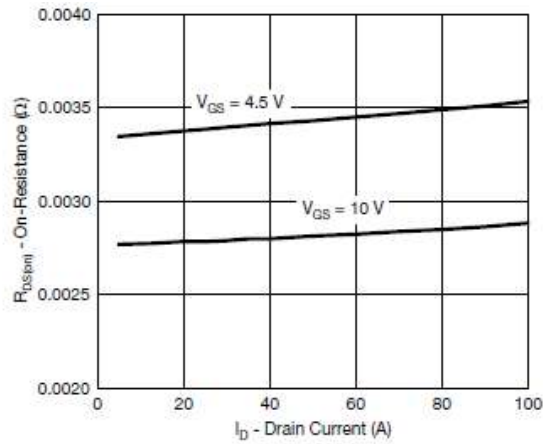
➤ **Electrical Characteristics ($T_J=25^\circ C$ Unless otherwise noted)**

Parameter	Symbol	Conditions	Min.	Typ	Max.	Unit
Static						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS}=0V, I_D=250\mu A$	40			V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	1.0		2.0	
Gate Leakage Current	I_{GSS}	$V_{DS}=0V, V_{GS}=\pm 20V$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=32V, V_{GS}=0V$			1	uA
		$V_{DS}=32V, V_{GS}=0V$ $T_J=85^\circ C$			10	
On-State Drain Current	$I_{D(on)}$	$V_{DS} \geq 10V, V_{GS}=10V$	50			A
Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS}=10V, I_D=25A$		2.78	3.3	m Ω
		$V_{GS}=4.5V, I_D=20A$		3.58	4.1	
Forward Transconductance	g_{FS}	$V_{DS}=15V, I_D=15A$		75		S
Diode Forward Voltage	V_{SD}	$I_S=10A, V_{GS}=0V$		0.85	1.3	V
Dynamic						
Total Gate Charge	Q_g	$V_{DS}=20V, V_{GS}=10V$ $I_D=20A$		60	100	nC
Gate-Source Charge	Q_{gs}			12		
Gate-Drain Charge	Q_{gd}			10		
Input Capacitance	C_{iss}	$V_{DS}=20V, V_{GS}=0V$ $f=1MHz$		4500		pF
Output Capacitance	C_{oss}			520		
Reverse Transfer Capacitance	C_{riss}			180		
Turn-On Time	$t_{d(on)}$	$V_{DD}=20V, R_L=2\Omega$ $I_D=10A, V_{GEN}=10V$ $R_G=1\Omega$		10	20	ns
	t_r			8	18	
Turn-Off Time	$t_{d(off)}$			40	75	
	t_f			8	18	

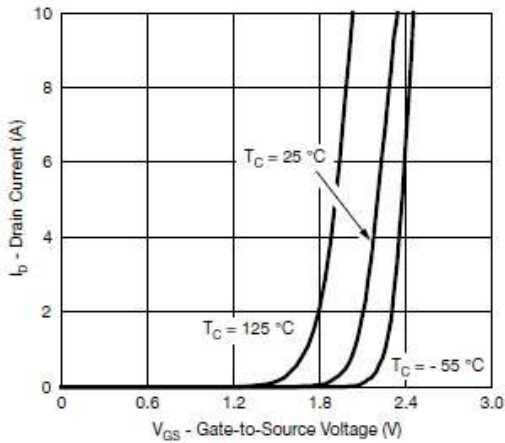
➤ Typical Characteristics



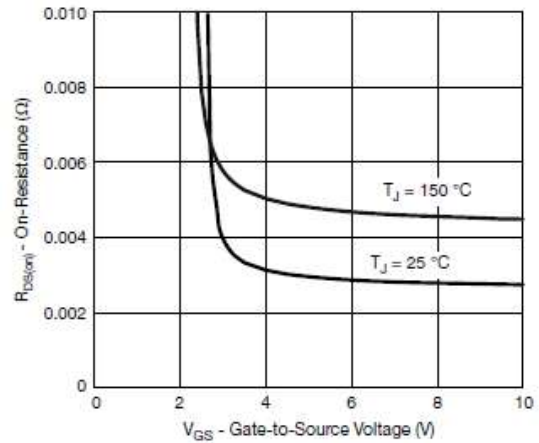
Output Characteristics



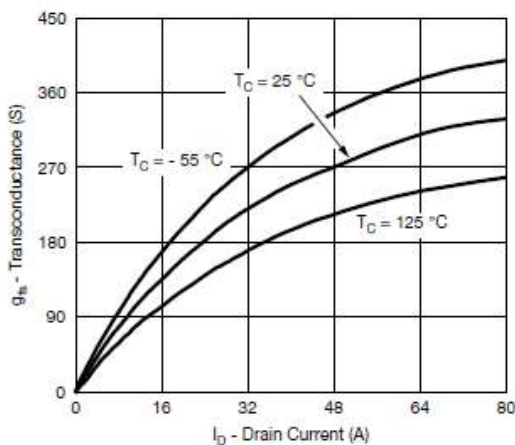
On-Resistance vs. Drain Current



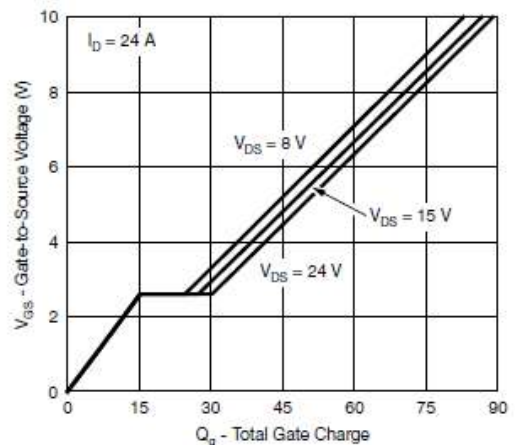
Transfer Characteristics



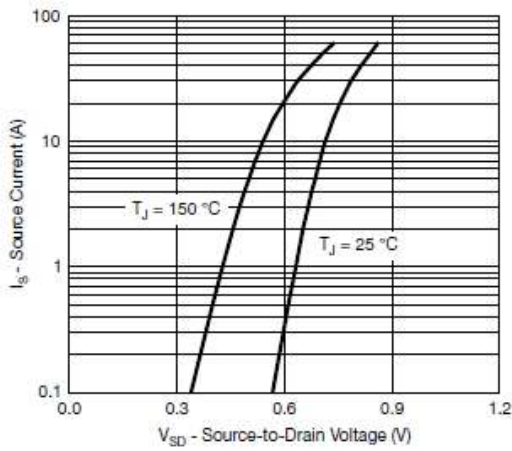
On-Resistance vs. Gate-to-Source Voltage



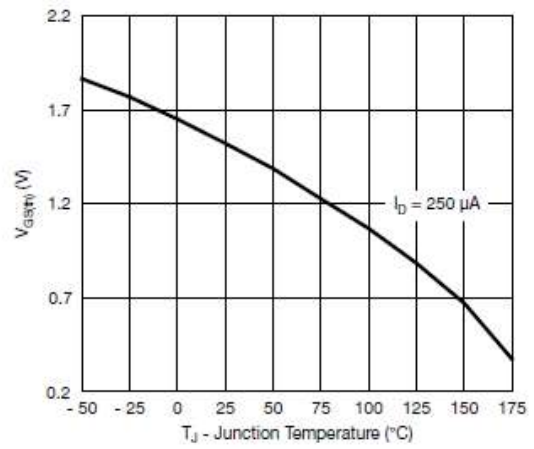
Transconductance



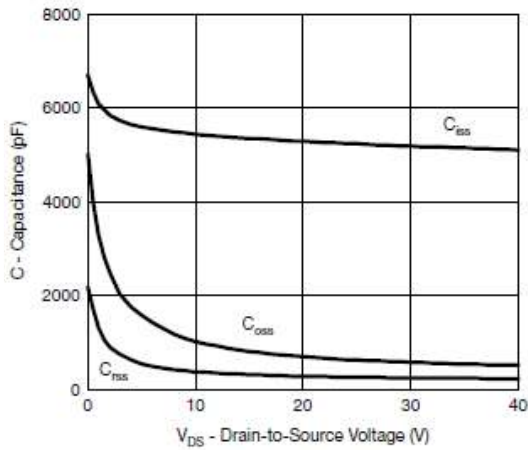
Gate Charge



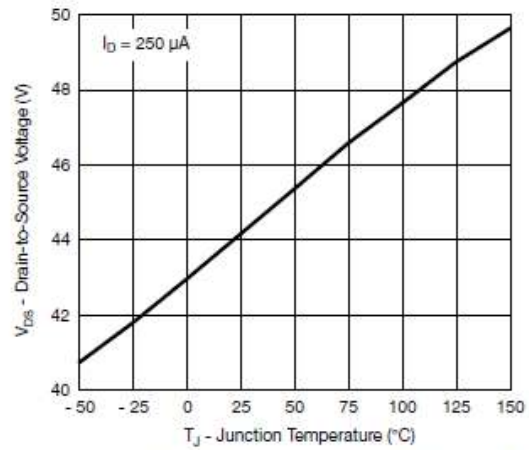
Source-Drain Diode Forward Voltage



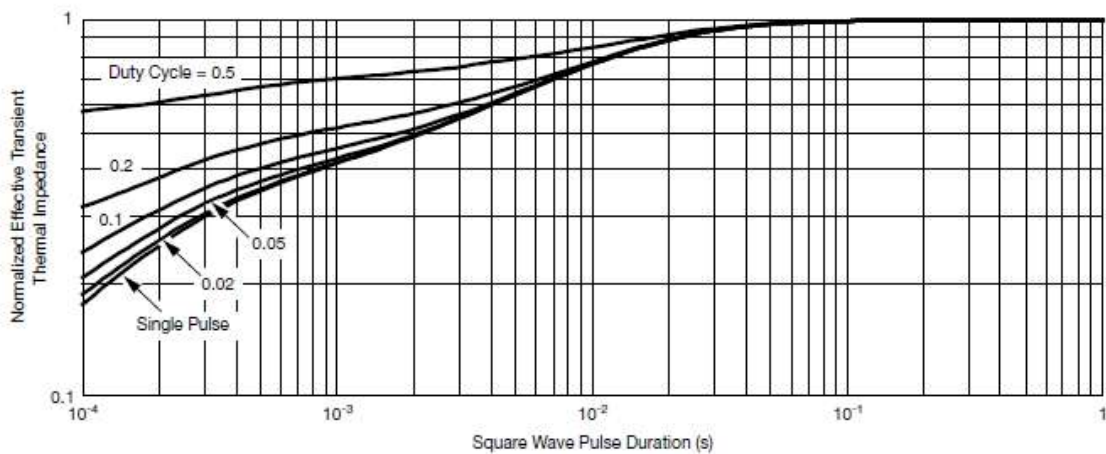
Threshold Voltage



Capacitance



Drain Source Breakdown vs. Junction Temperature



Normalized Thermal Transient Impedance, Junction-to-Case

➤ Recommand IR Reflow Soldering Thermal Profile

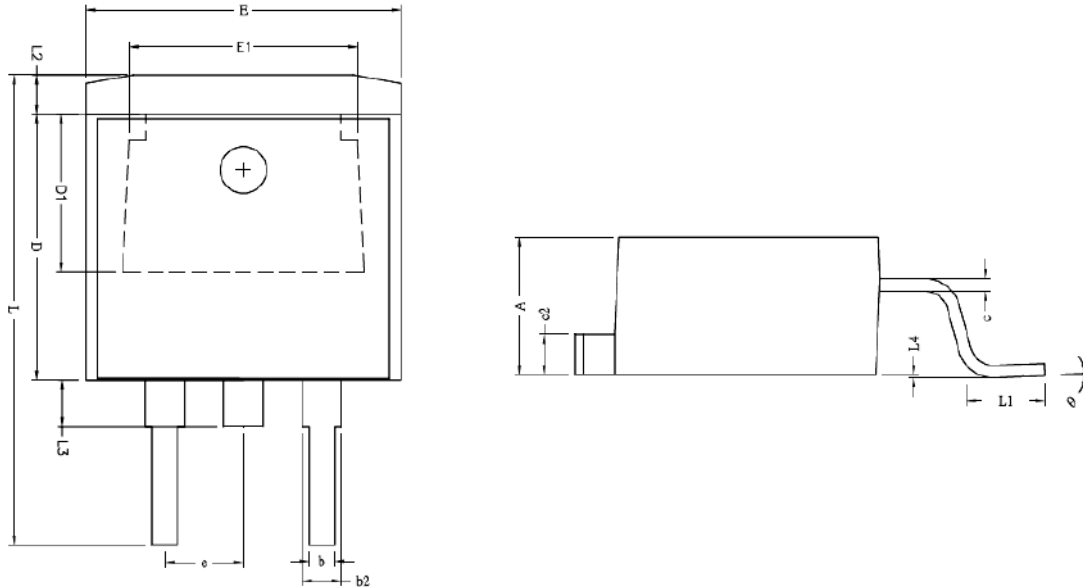


Profile Feature	Pb-Free Assembly Profile
Temperature Min. (T _{smin})	150°C
Temperature Max. (T _{smax})	200°C
Time (t _s) from (T _{smin} to T _{smax})	60-120 seconds
Average Ramp-up Rate (t _L to t _P)	3°C/second max.
Liquidous Temperature (T _L)	217°C
Time (t _L) Maintained Above (T _L)	60 – 150 seconds
Peak Temperature	260°C +0°C / -5°C
Time (t _P) within 5°C of actual Peak Temperature	30 seconds
Ramp-down Rate (T _P to T _L)	6°C/second max
Time 25°C to Peak Temperature	8 minutes max.

➤ Ordering Information

Part Number	Description	Quantity
PAN90TP04SP	TO-263-2L Reel	800

➤ Package Information (TO-263-2L)



REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	4.40	4.80	c2	1.25	1.45
b	0.76	1.0	b2	1.17	1.47
L4	0.00	0.254	D	8.6	9.0
c	0.36	0.50	D1	5.10 REF.	
L3	1.50 REF.		e	2.54 REF.	
L1	2.29	2.79	L	14.6	15.8
E	9.80	10.4	θ	$0^\circ \pm 3^\circ$	
E1	7.40 REF.		L2	1.27 REF.	

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